



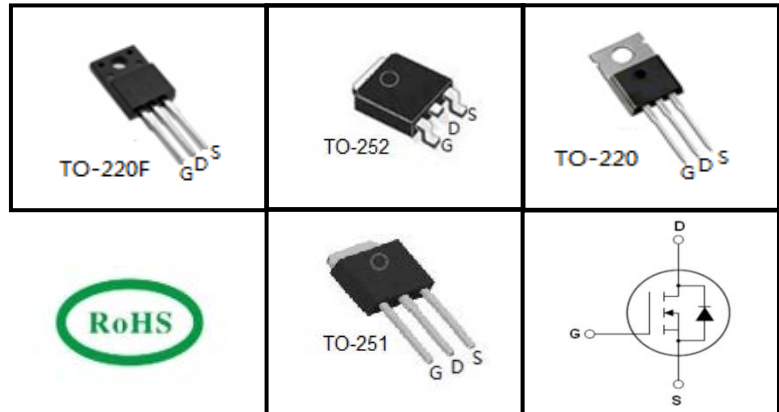
## 700V Super-Junction Power MOSFET

### FEATURES

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information				
Device	TPA70R360M	TPD70R360M	TPP70R360M	TPU70R360M
Package	TO-220F	TO-252	TO-220	TO-251
Marking	70R360M	70R360M	70R360M	70R360M

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted					
Parameter	Symbol	Value		Unit	
		TO-252,TO-220,TO-251	TO-220F		
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	700		V	
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	11		A
		$T_C = 100^\circ\text{C}$	6.6		
Pulsed Drain Current (note1)	$I_{DM}$	33		A	
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V	
Single Pulse Avalanche Energy (note2)	$E_{AS}$	215		mJ	
Avalanche Current (note1)	$I_{AR}$	1.8		A	
Repetitive Avalanche Energy (note1)	$E_{AR}$	0.32		mJ	
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50		V/ns	
Reverse diode dv/dt, $V_{DS} = 0 \dots 480\text{V}$ , $I_{SD} \leq I_D$	dv/dt	15		V/ns	
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	83	31	W	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ\text{C}$	

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-252,TO-220,TO-251	TO-220F	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.5	4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62	80	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 700V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 700V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.5A$	--	0.31	0.36	$\Omega$
Gate resistance	$R_G$	$f = 1.0\text{MHz}$ open drain	--	18	--	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	871	--	$\mu F$
Output Capacitance	$C_{oss}$		--	37	--	
Reverse Transfer Capacitance	$C_{rss}$		--	5	--	
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 11A,$ $V_{GS} = 10V$	--	22	--	nC
Gate-Source Charge	$Q_{gs}$		--	4	--	
Gate-Drain Charge	$Q_{gd}$		--	8	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 11A,$ $R_G = 25\Omega$	--	69.7	--	ns
Turn-on Rise Time	$t_r$		--	69.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	145	--	
Turn-off Fall Time	$t_f$		--	59	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	11	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	33	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 11A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	377	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	3.4	--	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		--	17.8	--	A

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 1.8A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

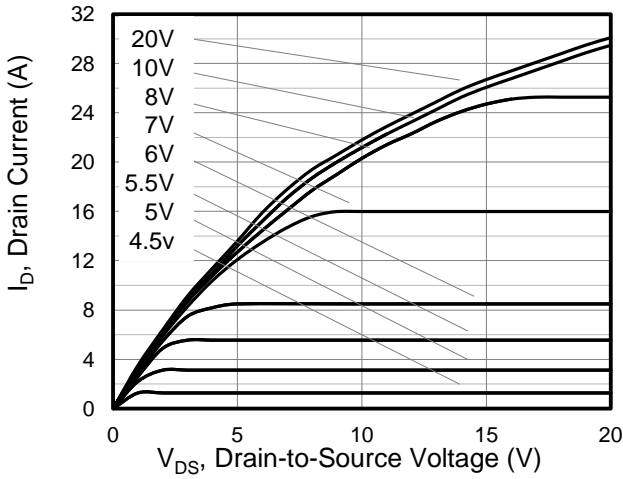


Figure 2. Transfer Characteristics

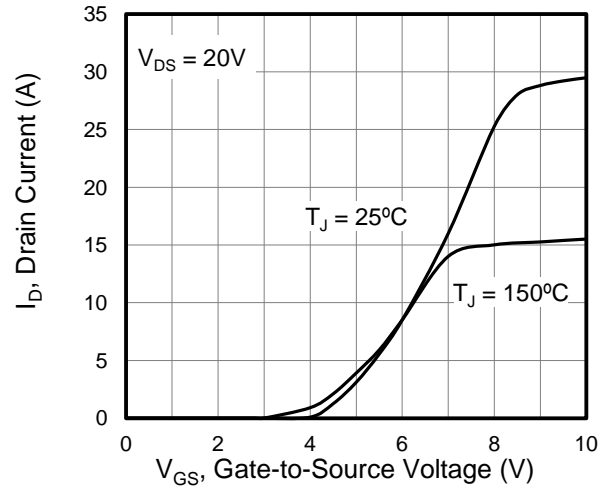


Figure 3. On-Resistance vs. Drain Current

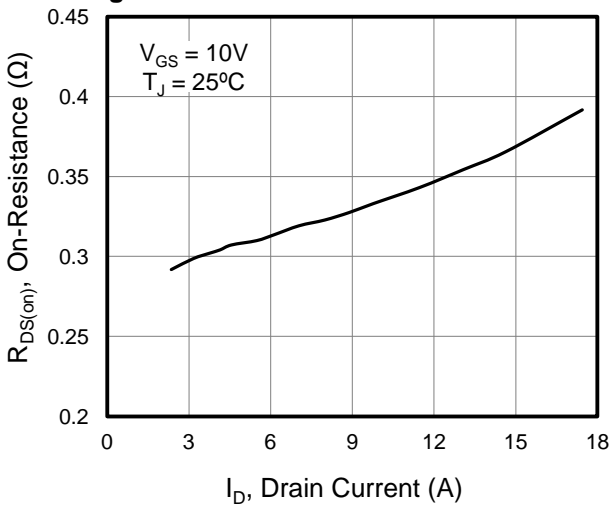


Figure 4. Capacitance

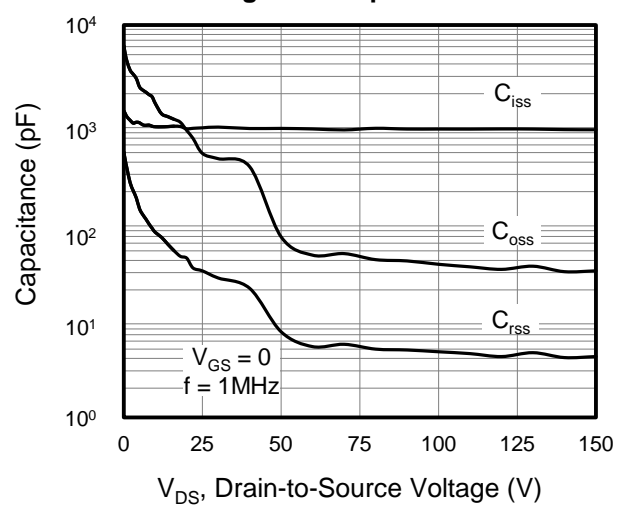


Figure 5. Gate Charge

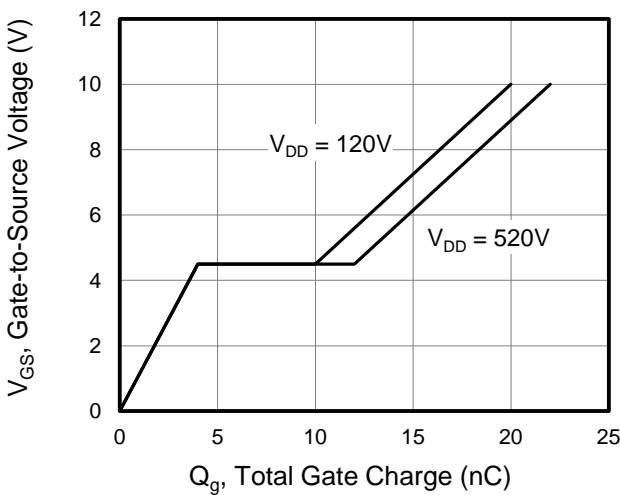
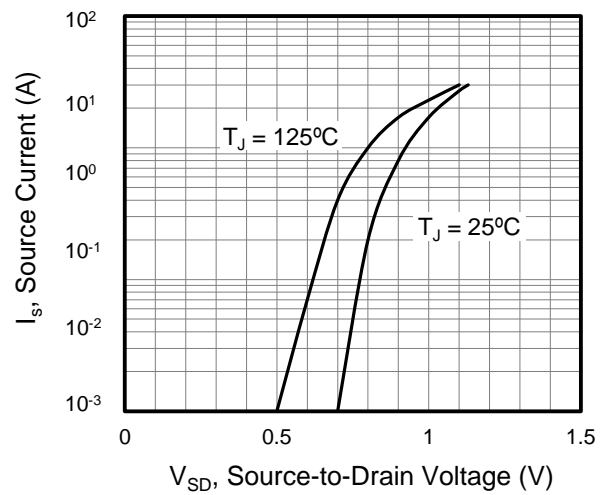


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

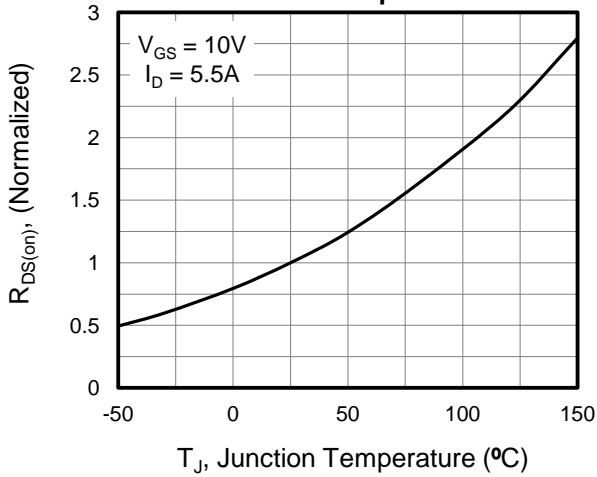


Figure 8. Breakdown voltage vs. Junction Temperature

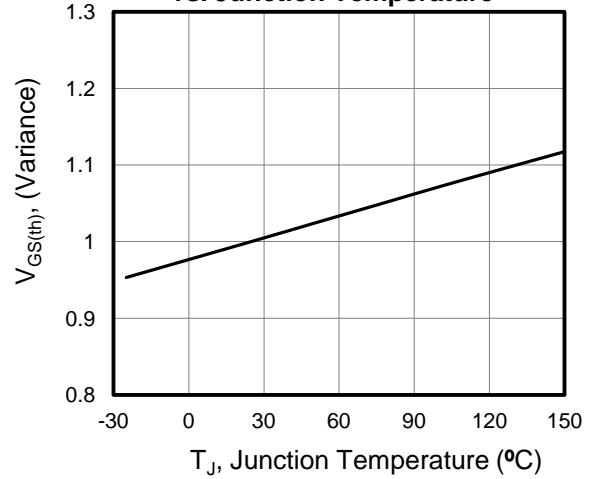


Figure 9. Transient Thermal Impedance TO-252/TO-220/TO-251

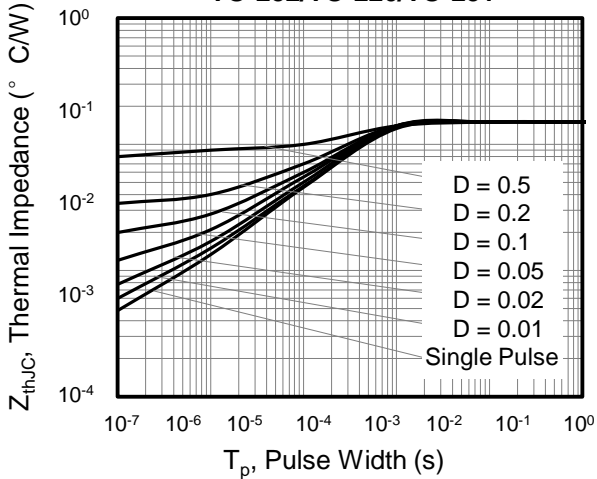


Figure 10. Transient Thermal Impedance TO-220F

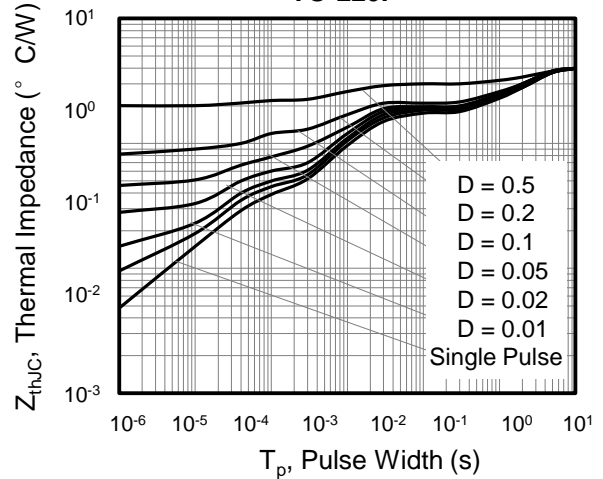


Figure 11. Safe operation area for TO-252/TO-220/TO-251

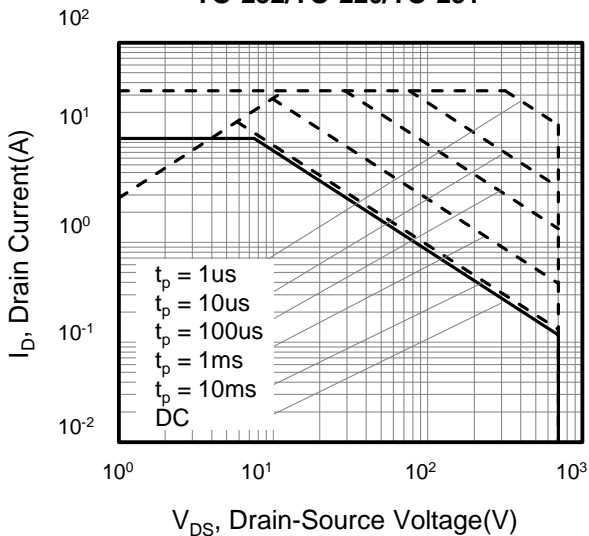


Figure 12. Safe operation area for TO-220F

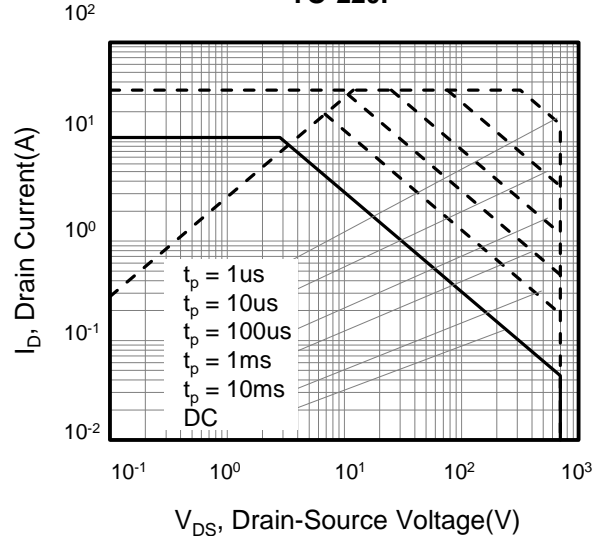




Figure A: Gate Charge Test Circuit and Waveform

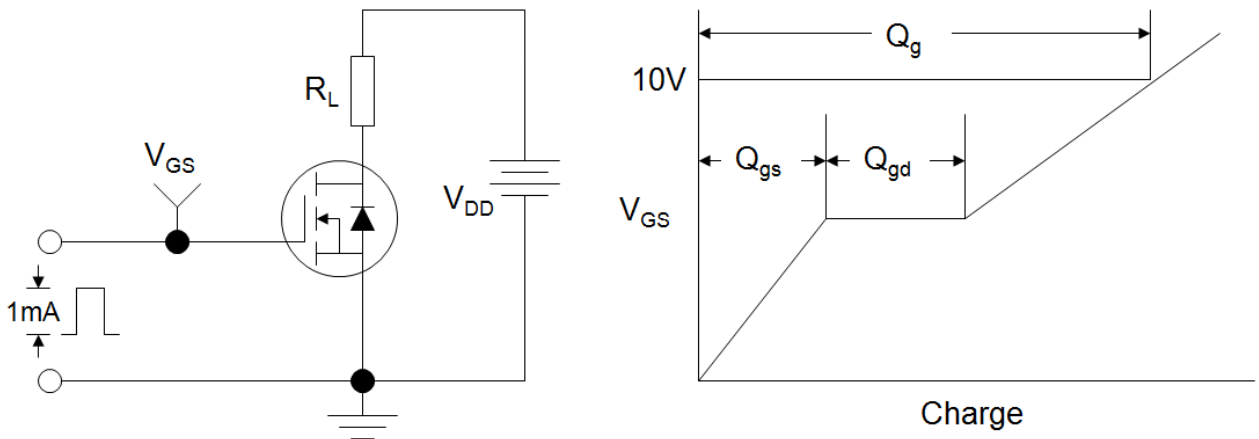


Figure B: Resistive Switching Test Circuit and Waveform

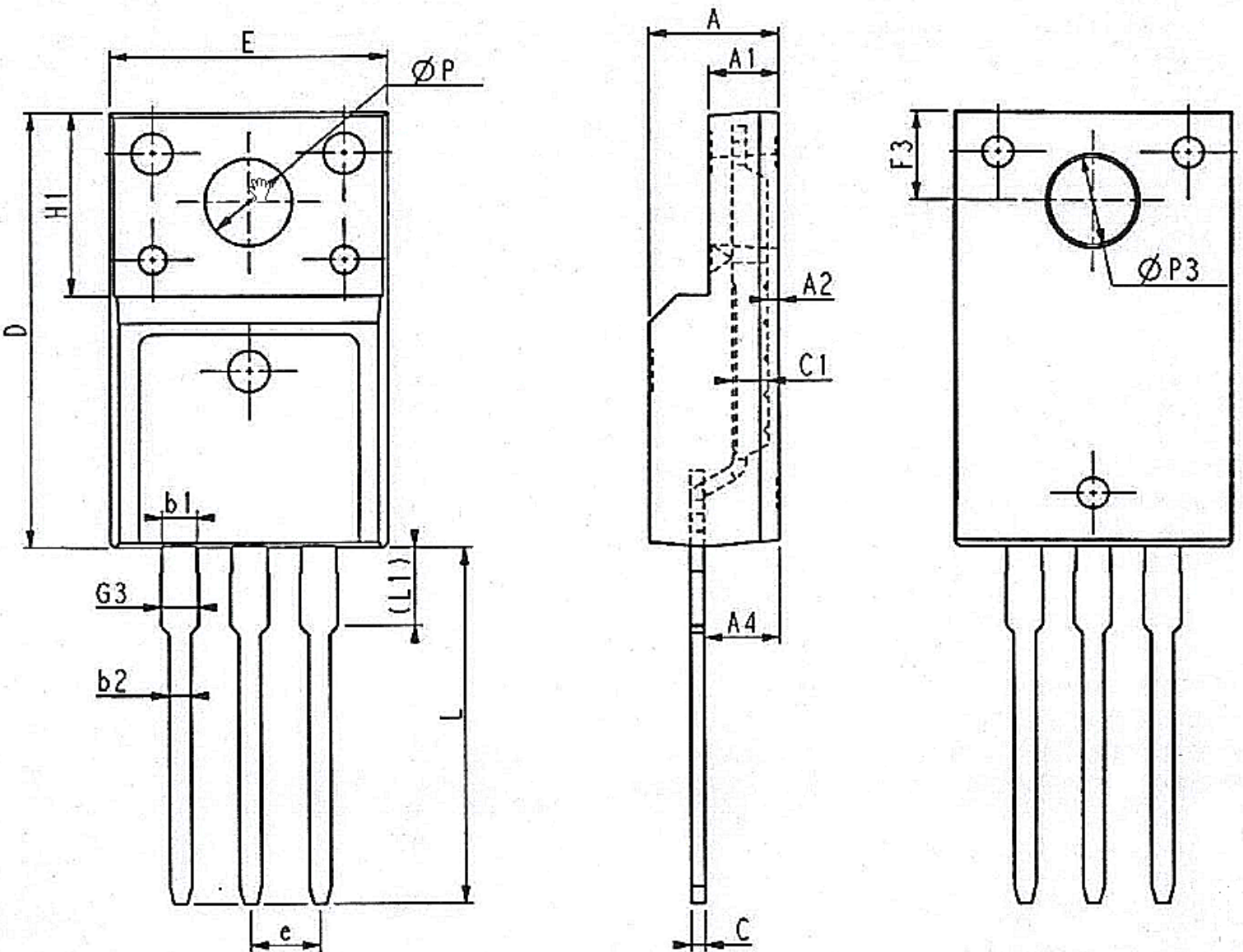


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





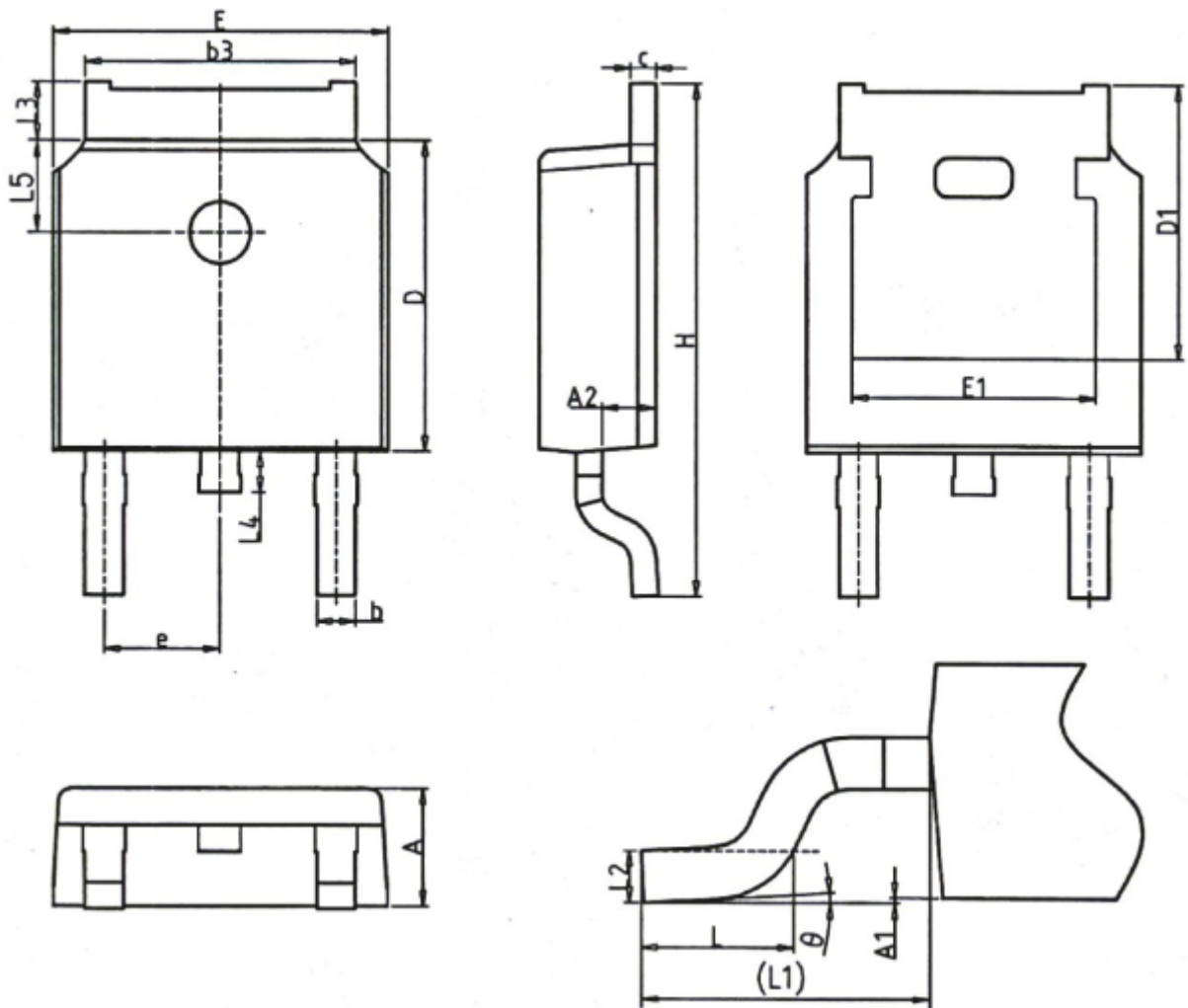
### TO-220F



Symbol	Min.	Nom	Max.	Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36	e	2.54BSC		
A	4.50	4.70	4.90	L	12.68	12.98	13.28
A1	2.34	2.54	2.74	L1	2.88	3.03	3.18
A2	0.30	0.45	0.60	$\Phi P$	3.03	3.18	3.38
A4	2.56	2.76	2.96	$\Phi P3$	3.15	3.45	3.65
c	0.40	0.50	0.65	F3	3.15	3.30	3.45
c1	1.20	1.30	1.35	G3	1.25	1.35	1.55
D	15.57	15.87	16.17	b1	1.18	1.28	1.43
H1	6.70REF			b2	0.70	0.80	0.95



## TO-252



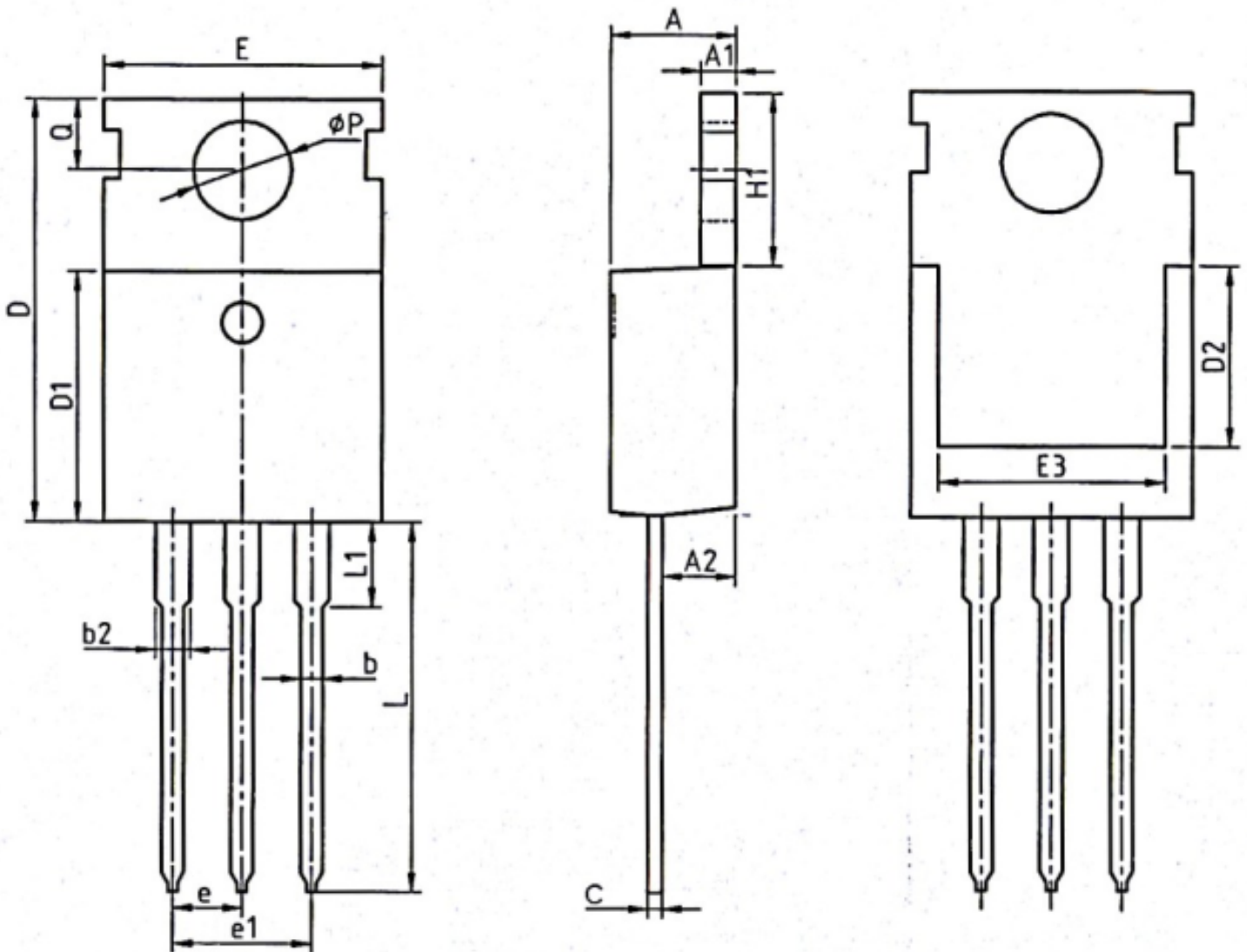
Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	-	-	1.00
L5	1.65	1.80	1.95
theta	0°	-	8°





## TO-220



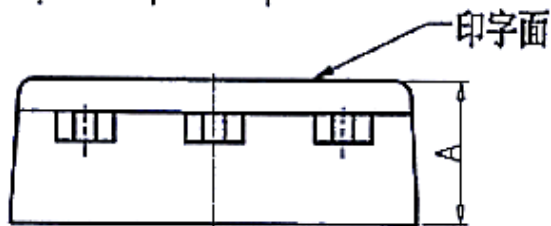
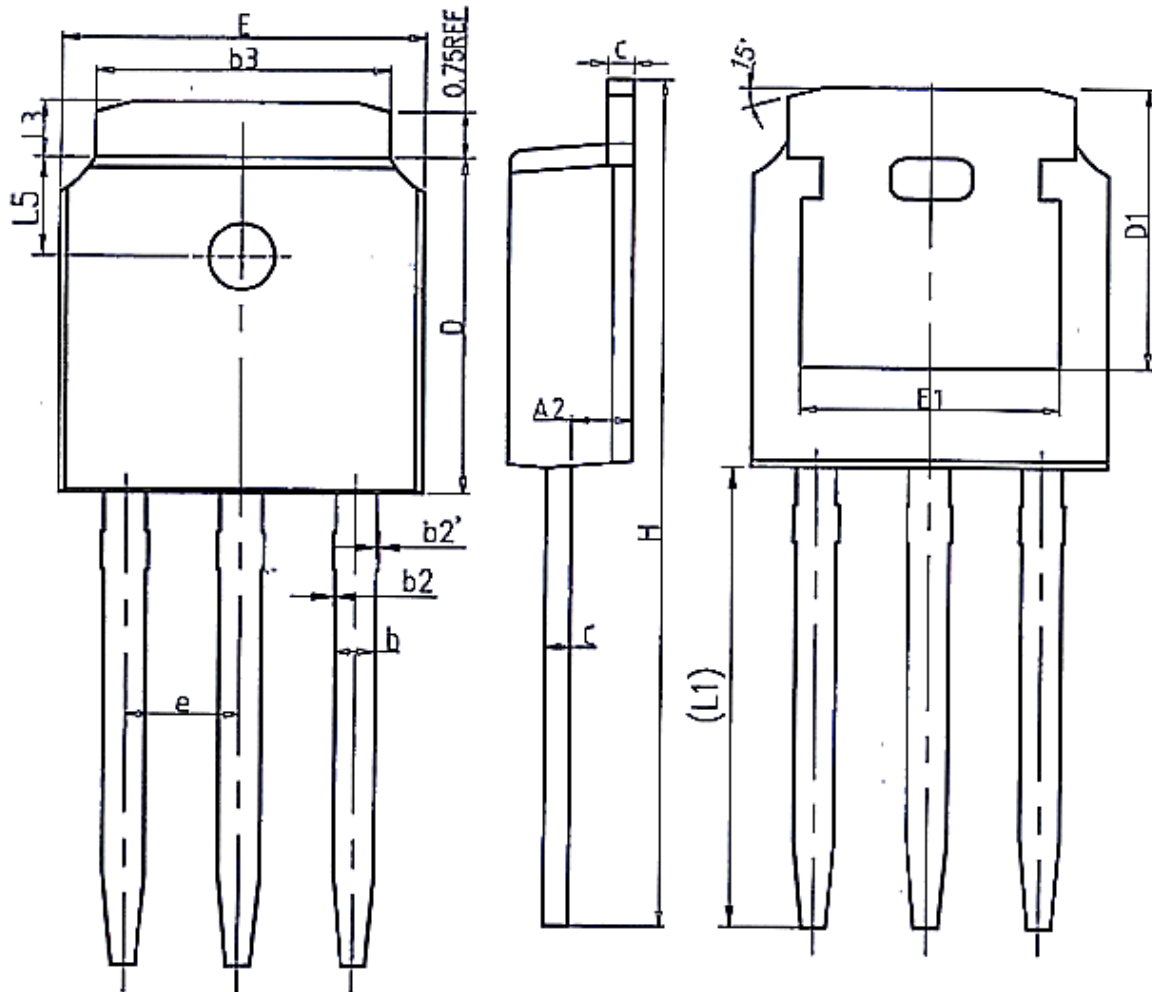
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
b	2.20	2.40	2.60
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30

Unit:mm			
Symbol	Min.	Nom	Max.
E3	7.00	-	-
e	2.54BSC		
e1	5.08BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00





### TO-251



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22

Unit:mm			
Symbol	Min.	Nom	Max.
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286 BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95



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